



Shantou Huashan Electronic Devices Co.,Ltd.

NPN SILICON TRANSISTOR

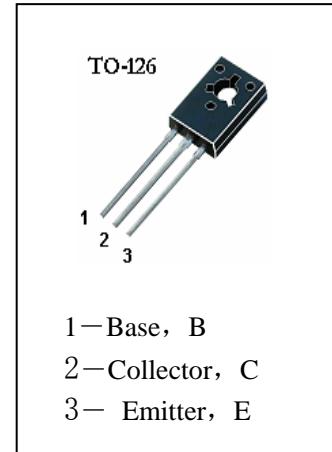
H13003H

■ HIGH VOLTAGE SWITCH MODE APPLICATIONS

High Speed Switching. Suitable for Switching Regulator and Motor Control

■ ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ\text{C}$)

T_{stg} —Storage Temperature.....	-65~150°C
T_j —Junction Temperature.....	150°C
P_C —Collector Dissipation.....	40W
V_{CBO} —Collector-Base Voltage.....	700V
V_{CEO} —Collector-Emitter Voltage.....	450V
V_{EBO} —Emitter-Base Voltage.....	9V
I_C —Collector Current.....	2A
I_B —Base Current.....	0.75A



■ ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BV_{CEO}	Collector-Emitter Breakdown Voltage	450			V	$I_C=5\text{mA}, I_B=0$
I_{EBO}	Emitter-Base Cut-off Current			10	μA	$V_{EB}=9\text{V}, I_C=0$
$hFE(1)$	DC Current Gain	10		40		$V_{CE}=5\text{V}, I_C=0.5\text{A}$
$hFE(2)$	DC Current Gain	5				$V_{CE}=2\text{V}, I_C=1\text{A}$
$V_{CE(sat)1}$	Collector- Emitter Saturation Voltage			0.5	V	$I_C=0.5\text{A}, I_B=0.1\text{A}$
$V_{CE(sat)2}$	Collector- Emitter Saturation Voltage			1	V	$I_C=1\text{A}, I_B=0.25\text{A}$
$V_{CE(sat)3}$	Collector- Emitter Saturation Voltage			2	V	$I_C=1.5\text{A}, I_B=0.5\text{A}$
$V_{BE(sat)1}$	Base-Emitter Saturation Voltage			1	V	$I_C=0.5\text{A}, I_B=0.1\text{A}$
$V_{BE(sat)2}$	Base-Emitter Saturation Voltage			1.2	V	$I_C=1\text{A}, I_B=0.25\text{A}$
f_T	Current Gain-Bandwidth Product	4			MHz	$V_{CE}=10\text{V}, I_C=0.1\text{A}$
t_{ON}	Turn On Time			1.1	μs	$V_{CC}=125\text{V}, I_C=1\text{A},$
t_{STG}	Storage Time			4.0	μs	$I_{B1}=0.2\text{A}, I_{B2}=-0.2\text{A}$
t_F	Fall Time			0.7	μs	$RL=125\Omega$

■ $hFE(1)$ Classification

H1	H2	H3	H4	H5
10-16	14-21	19-26	24-31	29-40



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■ Typical Characteristics

Fig 1. DC Current Gain

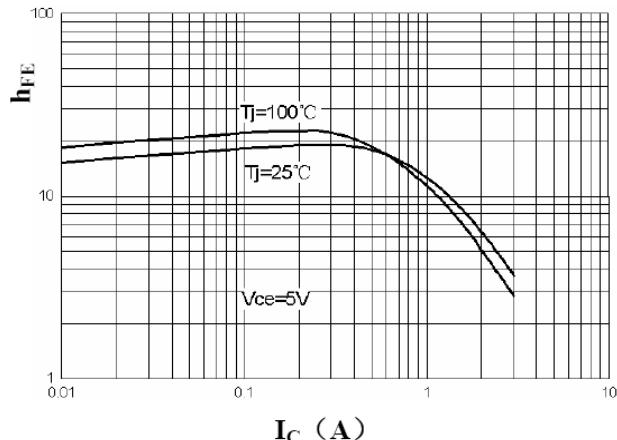


Fig 2. Collector-Emitter Saturation Voltage

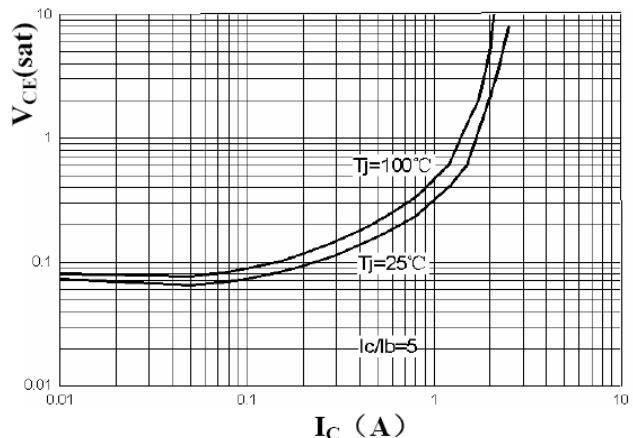


Fig 3. Base-Emitter Saturation Voltage

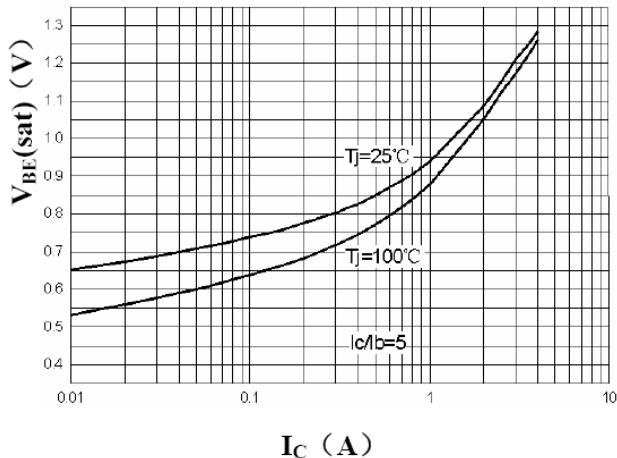


Fig 4. Safe Operation Areas

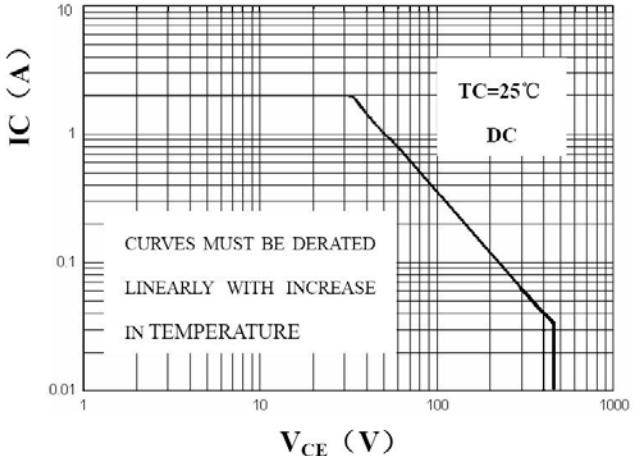
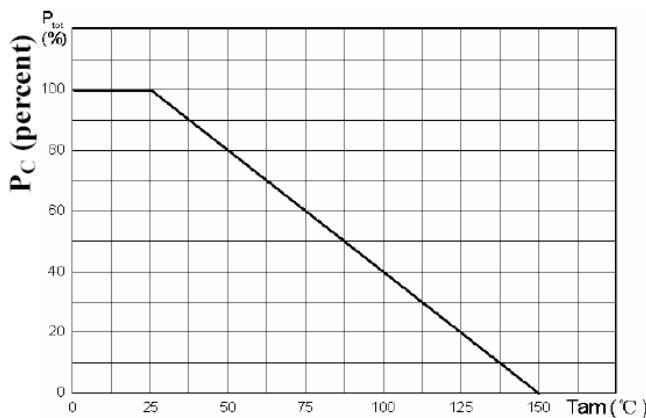


Fig 5. Power Derating Curve



T_C ($^\circ C$)

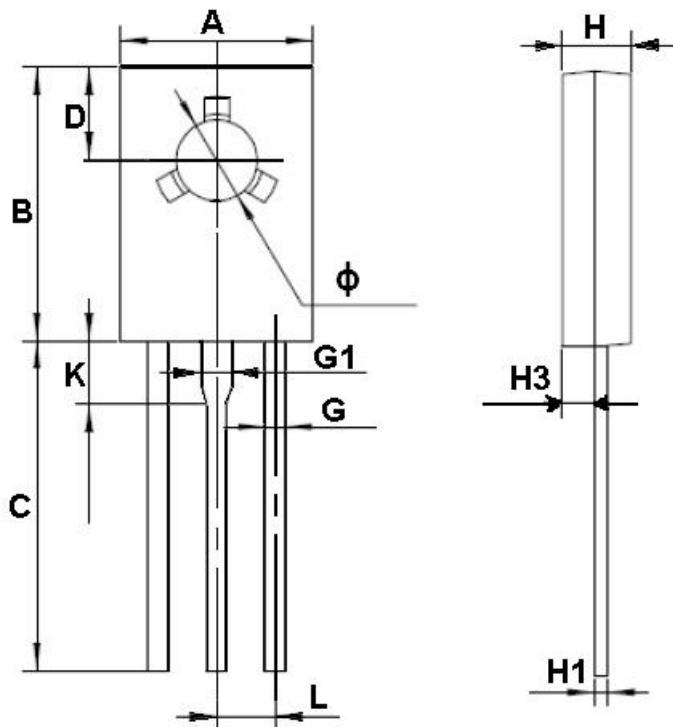


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■ Package Dimensions



SYMBOL	MILLIMETERS		SYMBOL	MILLIMETERS		SYMBOL	MILLIMETERS	
	Min	Max		Min	Max		Min	Max
A		8.5	G1	(1.2)		K	2.3	2.7
B		12.0	H		2.8	L		2.3
C	13.0		H1	0.49	0.57	φ	3.0	3.4
D	3.6	4.0	H3	(1.27)				
G	0.7	0.86						

Notes: () is for reference data.